

Pasziewicz Regina

List of Publications by Year in descending order

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49
all docs

49
docs citations

49
times ranked

298
citing authors

#	ARTICLE	IF	CITATIONS
1	A novel electrospun ZnO nanofibers biosensor fabrication. Sensors and Actuators B: Chemical, 2011, 160, 1413-1418.	4.0	41
2	SbSI Nanosensors: from Gel to Single Nanowire Devices. Nanoscale Research Letters, 2017, 12, 97.	3.1	23
3	SbSI nanowires for ferroelectric generators operating under shock pressure. Materials Letters, 2016, 180, 15-18.	1.3	19
4	Optimization of AlGaIn/GaN/Si(111) buffer growth conditions for nitride based HEMTs on silicon substrates. Journal of Crystal Growth, 2015, 414, 248-253.	0.7	16
5	Comparison of electrical, optical and structural properties of epitaxially grown HEMT's type AlGaIn/AlN/GaN heterostructures on Al ₂ O ₃ , Si and SiC substrates. Superlattices and Microstructures, 2016, 100, 619-626.	1.4	13
6	Nanostructuring of Si substrates by a metal-assisted chemical etching and dewetting process. RSC Advances, 2018, 8, 31224-31230.	1.7	13
7	Nondestructive method for evaluation of electrical parameters of AlGaIn/GaN HEMT heterostructures. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 490-493.	0.8	12
8	Stress engineering in GaN structures grown on Si(111) substrates by SiN masking layer application. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	0.9	10
9	Surface topography analysis with application of roughness area dependence method. Ultramicroscopy, 2016, 170, 77-85.	0.8	9
10	Surface electrical characterization of defect related inhomogeneities of AlGaIn/GaN/Si heterostructures using scanning capacitance microscopy. Materials Science in Semiconductor Processing, 2019, 94, 57-63.	1.9	7
11	Influence of growth process scheme on the properties of AlGaIn/AlN/GaN heterostructures. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 306-310.	0.8	6
12	<title>Applications of GaN-based materials in modern optoelectronics</title>. , 2004, , .		5
13	Stress control by micropits density variation in strained AlGaIn/GaN/SiN/AlN/Si(111) heterostructures. Crystal Research and Technology, 2016, 51, 225-230.	0.6	5
14	Microanalysis of the Ti/Al and Ti/Al/Mo/Au ohmic contacts metallization to AlGaIn/GaN heterostructures. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 1145-1149.	0.8	5
15	Scanning capacitance microscopy characterization of AlInBV epitaxial layers. Materials Science-Poland, 2016, 34, 845-850.	0.4	5
16	Growth Uniformity in Selective Area Epitaxy of AlGaIn/GaN Heterostructures for the Application in Semiconductor Devices. Electronics (Switzerland), 2020, 9, 2129.	1.8	5
17	GaN/AlN superlattice high electron mobility transistor heterostructures on GaN/Si(111). Physica Status Solidi (B): Basic Research, 2015, 252, 1195-1200.	0.7	4
18	Self-organization of palladium nanoislands on GaN and Al _x Ga _{1-x} N/GaN heterostructures. Applied Surface Science, 2017, 426, 123-132.	3.1	4

#	ARTICLE	IF	CITATIONS
19	Metalorganic vapour-phase epitaxy of AlGaIn/GaN heterostructures on chlorine plasma etched GaN templates without buried conductive layer. <i>Materials Science in Semiconductor Processing</i> , 2020, 107, 104816.	1.9	3
20	Correlation of Selected Problems During GaN MOCVD Epitaxy on Si Substrates with in-situ Interferometer Observation. <i>Journal of Electrical Engineering</i> , 2014, 65, 294-298.	0.4	3
21	Characterisation of AlGaIn MSM by Light Beam Induced Current technique. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 602-606.	0.8	2
22	Stability of ZnO nanofibers in processing liquid agents. <i>Materials Science-Poland</i> , 2013, 31, 312-317.	0.4	2
23	Formation Process and Properties of Ohmic Contacts Containing Molybdenum to AlGaIn/GaN Heterostructures. <i>Advances in Electrical and Electronic Engineering</i> , 2016, 14, .	0.2	2
24	Properties of GaN layers deposited on (0001) sapphire templates. , 2008, , .		1
25	The influence of contact mode on resolution in UV 400 lithography. , 2011, , .		1
26	Creation of high resolution pattern by nanoscratching. <i>Open Physics</i> , 2011, 9, .	0.8	1
27	Influence of hydrogen absorption on stress changes in thin catalytic metal films dedicated for sensors application. <i>Open Physics</i> , 2011, 9, .	0.8	1
28	Phase retrieval from the optical vortex scanning microscopy. , 2014, , .		1
29	Electron Beam Lithography Double Step Exposure Technique for Fabrication of Mushroom-Like Profile in Bilayer Resist System. <i>Journal of Electrical Engineering</i> , 2015, 65, 381-385.	0.4	1
30	Growth and coalescence control of inclined c-axis polar and semipolar GaN multilayer structures grown on Si(111), Si(112), and Si(115) by metalorganic vapor phase epitaxy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2016, 34, 051504.	0.9	1
31	Two-stage reactive ion etching of AlGaIn/GaN high electron mobility transistor type heterostructures. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2019, 37, 011204.	0.6	1
32	Application of Cl ₂ /BCl ₃ /Ar Plasma Treatment in the Improvement of Ti/Al/Mo/Au Ohmic Contacts. <i>Advances in Electrical and Electronic Engineering</i> , 2016, 14, .	0.2	1
33	Proximity Effect in Gate Fabrication Using Photolithography Technique. <i>Advances in Electrical and Electronic Engineering</i> , 2017, 15, .	0.2	1
34	AlGaIn/GaN Heterostructures Electrical Performance by Altering GaN/Sapphire Buffers Growth Pressure and Low-temperature GaN Interlayers Application. <i>Crystal Research and Technology</i> , 2021, 56, 2100090.	0.6	1
35	<title>Photoluminescence of GaAs grown by liquid phase epitaxy from Bi solution</title>. , 1997, , .		0
36	Application of GaN laterally overgrown on sapphire. , 2001, , .		0

#	ARTICLE	IF	CITATIONS
37	Optical properties of GaN layers grown by MOCVD. , 2001, 4413, 37.		0
38	Characterization of Ar+ based Ion Beam Etching of GaN. , 2006, , .		0
39	Functionally Graded Structures of AlIII-BV(N) Materials for Detectors. , 2006, , .		0
40	Impact of the initial stage of deposition conditions on the properties of subsequent GaN Layer. , 2007, , .		0
41	Simulation of the influence of grain structure of heteroepitaxial nitrides layers on the performance of MSM detector. , 2007, , .		0
42	Surface preparation for gallium nitride thick layers deposition by HVPE. , 2009, , .		0
43	Application of AFM microscope as a nanolithography tool. , 2010, , .		0
44	Application nanoindenter as nanolithography tool. , 2011, , .		0
45	Atomic force microscopy for low dimensional metal strips creation and measurements. , 2011, , .		0
46	The selection of gas chemistry in reactive ion etching of AlGaIn/GaN heterostructures. , 2011, , .		0
47	Investigation of the influence of low-concentration hydrogen on the surface potential of thin metallic films for sensor applications. Open Physics, 2011, 9, .	0.8	0
48	Different buffer approaches for AlGaIn/GaN heterostructures epitaxy on Si(111) substrates. , 2014, , .		0
49	Substrate Effect in Electron Beam Lithography. Advances in Electrical and Electronic Engineering, 2018, 16, .	0.2	0